Abstracts

General Noise Analysis for Bias- and RF-Voltage-Dependent Transferred-Electron Devices (Short Papers)

J.T. Patterson. "General Noise Analysis for Bias- and RF-Voltage-Dependent Transferred-Electron Devices (Short Papers)." 1976 Transactions on Microwave Theory and Techniques 24.7 (Jul. 1976 [T-MTT]): 460-463.

The general AM and FM noise spectrum analysis of Sweet for transferred-electron devices is extended to include the variation of device admittance with both bias- and RF-voltage amplitudes. This is important because recent investigations by the author suggest that there are significant variations of device admittance with both parameters. Also the expressions for the AM and FM noise spectra are formulated in terms of the more basic quantities such as stored charge, modulation sensitivities, and incremental admittance.

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